

Designed for ultra broadband high power applications, this amplifier utilizes linear Silicon RF Power MOSFET devices that provide high gain, wide dynamic range and good linearity. Exceptional performance, long term reliability and high efficiency are achieved by employing advanced broadband RF matching networks and combining techniques, EMI/RFI filters, custom-machined housings and qualified components. Each unit undergoes extensive burn-in prior to final test and inspection.

**ELECTRICAL SPECIFICATIONS @ 28 VDC, 25°C**

Characteristics	Rating	Limit
Frequency Response	10 – 1000 MHz	Min
Power Output CW	25 Watts	Min
Power Output @ 1 dB comp.	12 Watts	Min
Small Signal Gain	46 dB	Min
Small Signal Gain Flatness	±1.5 dB	Max
Third Order Intercept Point	+50 dBm	Typ
Input Overdrive	+10 dBm	Max
Input/Output VSWR @ 50 ohm	2:1	Max
Harmonics @ 1 dB compression	-20 dBc	Typ
Noise Figure	10 dB	Max
Spurious Signals	-60 dBc	Max
Supply Voltage	28 VDC	Nom
Current Consumption	4.0 Amp	Max

**ENVIRONMENTAL CHARACTERISTICS**

Operating Temperature: 0°C to +50°C  
 Non-operating Temperature: -40°C to +85°C  
 Humidity: 95% relative without condensation  
 Altitude: 10,000 feet  
 Shock and Vibration: Normal truck transport

**CIRCUIT PROTECTIONS**

Infinite Load VSWR  
 RF Input Overdrive  
 Thermal Overload

**MECHANICAL SPECIFICATIONS**

Dimensions	6.4"x3.4"x1.1"	Max
Weight	1.0 lb.	Max
RF Connectors	SMA female	
Cooling	External Heatsink	

